WÅ‚odzimierz Nakwaski

List of Publications by Year
in descending order

182 papers	1,614 citations	331642 21 h-index	395678 33 g-index
183 all docs	183 docs citations	183 times ranked	768 citing authors

#	ARTICLE	IF	CITATIONS
1	Thermal conductivity of binary, ternary, and quaternary IIIâ€V compounds. Journal of Applied Physics, 1988, 64, 159-166.	2.5	154
2	Effective masses of electrons and heavy holes in GaAs, InAs, A1As and their ternary compounds. Physica B: Condensed Matter, 1995, 210, 1-25.	2.7	98
3	Thermal properties of etched-well surface-emitting semiconductor lasers. IEEE Journal of Quantum Electronics, 1991, 27, 1391-1401.	1.9	73
4	Thermal resistance of top-surface-emitting vertical-cavity semiconductor lasers and monolithic two-dimensional arrays. Electronics Letters, 1992, 28, 572.	1.0	62
5	Optimization of 1.3 Âµm GaAs-based oxide-confined (GaIn)(NAs) vertical-cavity surface-emitting lasers for low-threshold room-temperature operation. Journal of Physics Condensed Matter, 2004, 16, S3121-S3140.	1.8	59
6	Transient thermal properties of high-power diode laser bars. Applied Physics Letters, 2006, 89, 263506.	3.3	42
7	Thermal analysis of the catastrophic mirror damage in laser diodes. Journal of Applied Physics, 1985, 57, 2424-2430.	2.5	39
8	Thermal analysis of GaAs-AlGaAs etched-well surface-emitting double-heterostructure lasers with dielectric mirrors. IEEE Journal of Quantum Electronics, 1993, 29, 1981-1995.	1.9	35
9	Thermal resistance of light-emitting diodes. IEEE Transactions on Electron Devices, 1985, 32, 2282-2291.	3.0	34
10	Thermal aspects of efficient operation of vertical-cavity surface-emitting lasers. Optical and Quantum Electronics, 1996, 28, 335-352.	3.3	34
11	Transverse modes in gain-guided vertical-cavity surface-emitting lasers. Optics Communications, 1998, 148, 63-69.	2.1	32
12	Effective thermal conductivity analysis of 1.55 Î¼m InGaAsP/InP vertical-cavity top-surface-emitting microlasers. Electronics Letters, 1993, 29, 1015-1016.	1.0	31
13	Oxidation kinetics of AlAs and (AlGa)As layers in GaAs-based diode laser structures: comparative analysis of available experimental data. Semiconductor Science and Technology, 2004, 19, 333-341.	2.0	30
14	Thermal analysis of closely-packed two-dimensional etched-well surface-emitting laser arrays. IEEE Journal of Selected Topics in Quantum Electronics, 1995, 1, 681-696.	2.9	28
15	Thermal crosstalk in arrays of III-N-based Lasers. Materials Science and Engineering B: Solid-State Materials for Advanced Technology, 2013, 178, 1395-1402.	3.5	27
16	THERMAL EFFECTS IN VERTICAL-CAVITY SURFACE-EMITTING LASERS. International Journal of High Speed Electronics and Systems, 1994, 05, 667-730.	0.7	25
17	Self-consistent model of 650 nm GaInP/AlGaInP quantum-well vertical-cavity surface-emitting diode lasers. Semiconductor Science and Technology, 2007, 22, 593-600.	2.0	25
18	III: Thermal Properties of Vertical-Cavity Surface-Emitting Semiconductor Lasers. Progress in Optics, 1998, 38, 165-262.	0.6	24

#	ARTICLE	IF	CITATIONS
19	Thermal model of the catastrophic degradation of highâ€power stripeâ€geometry GaAs/(AlGa)As doubleâ€heterostructure diode lasers. Journal of Applied Physics, 1990, 67, 1659-1668.	2.5	23
20	Comprehensive self-consistent three-dimensional simulation of an operation of the GaAs-based oxide-confined 1.3-Î¼m quantum-dot (InGa)As/GaAs vertical-cavity surface-emitting lasers. Optical and Quantum Electronics, 2004, 36, 331-347.	3.3	23
21	Numerical Self-Consistent Analysis of VCSELs. Advances in Optical Technologies, 2012, 2012, 1-17.	0.8	23
22	Room-temperature continuous-wave operation of the In(Ga)As/GaAs quantum-dot VCSELs for the 1.3 Âµm optical-fibre communication. Semiconductor Science and Technology, 2009, 24, 055003.	2.0	22
23	Thermal properties of the Burrus-type light-emitting diode: Part Iâ€"The model. IEEE Transactions on Electron Devices, 1986, 33, 889-899.	3.0	19
24	Carrier diffusion inside active regions of gain-guided vertical-cavity surface-emitting lasers. IEE Proceedings: Optoelectronics, 1997, 144, 421-425.	0.8	18
25	Temperature and thickness dependence of steam oxidation of AlAs in cylindrical mesa structures. IEEE Photonics Technology Letters, 2001, 13, 687-689.	2.5	18
26	Thermal model of laser diode arrays. Electronics Letters, 1986, 22, 1169.	1.0	18
27	Static thermal properties of broad-contact double-heterostructure laser diodes. Optical and Quantum Electronics, 1983, 15, 513-527.	3.3	17
28	Designing guidelines for possible continuous-wave-operating nitride vertical-cavity surface-emitting lasers. Journal Physics D: Applied Physics, 2000, 33, 642-653.	2.8	16
29	Separate-confinement-oxidation vertical-cavity surface-emitting laser structure. Journal of Applied Physics, 2006, 99, 123110.	2.5	16
30	Microthermography of diode lasers: The impact of light propagation on image formation. Journal of Applied Physics, 2009, 105, 014502.	2.5	16
31	Precise Lateral Mode Control in Photonic Crystal Vertical-Cavity Surface-Emitting Lasers. IEEE Journal of Quantum Electronics, 2011, 47, 1291-1296.	1.9	16
32	An appreciation of usability of the finite element method for the thermal analysis of stripe-geometry diode lasers. Journal of Thermal Analysis, 1990, 36, 1171-1189.	0.6	15
33	Spreading resistance in protonâ€implanted verticalâ€cavity surfaceâ€emitting diode lasers. Applied Physics Letters, 1992, 61, 3101-3103.	3.3	15
34	Optimal photonic-crystal parameters assuring single-mode operation of 1300 nm AlInGaAs vertical-cavity surface-emitting laser. Journal of Applied Physics, 2009, 105, 093102.	2.5	15
35	Detailed threshold analysis of UV-emitting nitride vertical-cavity surface-emitting lasers. Journal Physics D: Applied Physics, 1998, 31, 2479-2484.	2.8	14
36	An impact of multi-layered structures of modern optoelectronic devices on their thermal properties. Optical and Quantum Electronics, 2008, 40, 205-216.	3.3	14

#	Article	IF	Citations
37	VCSEL structures used to suppress higher-order transverse modes. Opto-electronics Review, 2011, 19, .	2.4	14
38	Some aspects of designing an efficient nitride VCSEL resonator. Journal Physics D: Applied Physics, 2001, 34, 954-958.	2.8	13
39	Three-dimensional time-dependent thermal model of catastrophic mirror damage in stripe-geometry double-heterostructure GaAs/(AlGa)As diode lasers. Optical and Quantum Electronics, 1989, 21, 331-334.	3.3	12
40	Thermal properties of the Burrus-type light-emitting diode: Part IIâ€"The results. IEEE Transactions on Electron Devices, 1986, 33, 900-907.	3.0	11
41	Current spreading and series resistance of proton-implanted vertical-cavity top-surface-emitting lasers. Applied Physics A: Materials Science and Processing, 1995, 61, 123-127.	2.3	11
42	Strong modes discrimination and low threshold in cw regime of 1300 nm AlInGaAs/InP VCSEL induced by photonic crystal. Physica Status Solidi (A) Applications and Materials Science, 2009, 206, 1396-1403.	1.8	11
43	Investigation of temperature characteristics of modern InAsP/InGaAsP multi-quantum-well TJ-VCSELs for optical fibre communication. Opto-electronics Review, 2011, 19, .	2.4	11
44	Comprehensive and fully self-consistent modeling of modern semiconductor lasers. Journal of Semiconductors, 2016, 37, 024001.	3.7	11
45	Temperature Profiles in Etched-Well Surface-Emitting Semiconductor Lasers. Japanese Journal of Applied Physics, 1991, 30, L596-L598.	1.5	10
46	Comparison of Exactness of Scalar and Vectorial Optical Methods Used to Model a VCSEL Operation. IEEE Journal of Quantum Electronics, 2007, 43, 399-406.	1.9	10
47	Comparison of Usability of Oxide Apertures and Photonic Crystals Used to Create Radial Optical Confinements in 650-nm GaInP VCSELs. IEEE Journal of Quantum Electronics, 2007, 43, 1041-1047.	1.9	10
48	An attempt to design long-wavelength (>2 Î¼m) InP-based GaInNAs diode lasers. Applied Physics A: Materials Science and Processing, 2012, 108, 521-528.	2.3	10
49	Dynamical thermal properties of broad-contact double-heterostructure GaAs-(AlGa)As laser diodes. Optical and Quantum Electronics, 1983, 15, 313-324.	3.3	9
50	Spreading thermal resistance of the heat-sink of a light-emitting diode. Solid-State Electronics, 1984, 27, 823-824.	1.4	9
51	On the thermal resistance of vertical-cavity surface-emitting lasers. Optical and Quantum Electronics, 1997, 29, 883-892.	3.3	9
52	Thermal properties of buried-heterostructure laser diodes. IEE Proceedings, Part J: Optoelectronics, 1987, 134, 87.	0.4	8
53	Finite-element thermal model for buried-heterostructure diode lasers. Optical and Quantum Electronics, 1994, 26, 87-95.	3.3	8
54	The spatial hole burning effect in gain-guided vertical-cavity surface-emitting lasers. Journal Physics D: Applied Physics, 1998, 31, L11-L15.	2.8	8

#	Article	IF	Citations
55	Transverse-mode selectivity in possible nitride vertical-cavity surface-emitting lasers. Optical and Quantum Electronics, 2003, 35, 1037-1054.	3.3	8
56	Usability limits of the scalar effective frequency method used to determine modes distributions in oxide-confined vertical-cavity surface-emitting diode lasers. Journal Physics D: Applied Physics, 2006, 39, 30-35.	2.8	8
57	Principles of VCSEL designing. Opto-electronics Review, 2008, 16, .	2.4	8
58	Analysis of Threshold Currents and Transverse Modes in Nitride VCSELs With Different Resonators. IEEE Journal of Quantum Electronics, 2016, 52, 1-7.	1.9	8
59	Tuning of reflection spectrum of a monolithic high-contrast grating by variation of its spatial dimensions. Optics Express, 2020, 28, 20967.	3.4	8
60	Threeâ€dimensional analysis of a heatâ€spreading phenomenon in phaseâ€locked arrays of oxideâ€isolated diode lasers. Journal of Applied Physics, 1990, 67, 2711-2715.	2.5	7
61	Heat-source distribution in etched-well surface-emitting semiconductor lasers. IEEE Photonics Technology Letters, 1991, 3, 979-981.	2.5	7
62	A novel diagonal-current injection VCSEL design proposed for nitride lasers. Semiconductor Science and Technology, 2001, 16, 598-602.	2.0	7
63	The modified kÂ·p method to investigate polarization effects in nitride quantum-well devices. Physica E: Low-Dimensional Systems and Nanostructures, 2005, 25, 504-514.	2.7	7
64	Visualization of heat flows in high-power diode lasers by lock-in thermography. Applied Physics Letters, 2008, 92, 103513.	3.3	7
65	Enhanced single-fundamental LP01 mode operation of 650-nm GaAs-based GaInP/AlGaInP quantum-well VCSELs. Applied Physics A: Materials Science and Processing, 2010, 98, 651-657.	2.3	7
66	A method used to overcome polarization effects in semi-polar structures of nitride light-emitting diodes emitting green radiation. Applied Physics A: Materials Science and Processing, 2013, 113, 801-809.	2.3	7
67	Thermal analysis of etched-well surface-emitting diode lasers. Microwave and Optical Technology Letters, 1991, 4, 541-543.	1.4	6
68	Mode transformation enhanced in nitride diode lasers by modification of their buffer layers. Journal Physics D: Applied Physics, 2001, 34, 1277-1285.	2.8	6
69	Threshold simulation of 1.3-Î¼m oxide-confined in-plane quantum-dot (InGa)As/GaAs lasers. Optical and Quantum Electronics, 2003, 35, 675-692.	3.3	6
70	Tuning effects in optimisation of GaAs-based InGaAs/GaAs quantum-dot VCSELs. Optics Communications, 2008, 281, 3163-3170.	2.1	6
71	Microphotoluminescence investigation of InAs quantum dot active region in 1.3â€‚Î¼m vertical cavity surface emitting laser structure. Journal of Applied Physics, 2010, 108, 073111.	2.5	6
72	Cavity designs for nitride VCSELs with dielectric DBRs operating efficiently at different temperatures. Optics and Laser Technology, 2020, 132, 106482.	4.6	6

#	Article	IF	Citations
73	The thermal properties of a single-heterostructure laser diode supplied with short current pulses. Optical and Quantum Electronics, 1979, 11, 319-327.	3.3	5
74	Output power saturation in InAs/GaAs quantum dot lasers. Physica Status Solidi C: Current Topics in Solid State Physics, 2003, 0, 1351-1354.	0.8	5
75	Thermal and molecular stresses in multi-layered structures of nitride devices. Semiconductor Science and Technology, 2003, 18, 733-737.	2.0	5
76	Analysis of anticipated performance of 650-nm GaInP/AlGaInP quantum-well GaAs-based VCSELs at elevated temperatures. Opto-electronics Review, 2008, 16, .	2.4	5
77	Physics of mode selectivity of vertical-cavity surface-emitting diode lasers. Journal of Applied Physics, 2010, 108, 044501.	2.5	5
78	Spatial-Mode Discrimination in Guided and Antiguided Arrays of Long-Wavelength VCSELs. IEEE Journal of Selected Topics in Quantum Electronics, 2013, 19, 1-10.	2.9	5
79	Temperature distribution in a light-emitting diode during a pulse operation. Electronics Letters, 1984, 20, 984.	1.0	4
80	Design guidelines for fundamental-mode-operated cascade nitride VCSELs. IEEE Photonics Technology Letters, 2003, 15, 495-497.	2.5	4
81	Fully self-consistent threshold model of one-dimensional arrays of edge-emitting nitride diode lasers. Semiconductor Science and Technology, 2004, 19, 997-1004.	2.0	4
82	Exactness of simplified scalar optical approaches in modelling a threshold operation of possible nitride verticalâ€cavity surfaceâ€emitting diode lasers. Physica Status Solidi (A) Applications and Materials Science, 2007, 204, 3562-3573.	1.8	4
83	Simulation of an operation of zinc oxide lightâ€emitting diodes. Microwave and Optical Technology Letters, 2011, 53, 2086-2090.	1.4	4
84	Thermal Effects Occurring in Semiconductor Lasers. , 1991, , 400-423.		4
85	Simplified thermal analysis of a laser diode array. Soviet Journal of Quantum Electronics, 1984, 14, 266-267.	0.1	3
86	How many quantum wells in nitride lasers?. Journal Physics D: Applied Physics, 2001, 34, 2346-2352.	2.8	3
87	Temperature-enhanced radial current spreading in possible VCSEL structures of nitride lasers. Semiconductor Science and Technology, 2002, 17, 255-260.	2.0	3
88	GaInNAsSb/GaNAs quantum-well VCSELs: Modeling and physical analysis in the 1.50â^'1.55â€‰Î¼m wavelength range. Journal of Applied Physics, 2007, 101, 073103.	2.5	3
89	Computer simulation of an operation of the GaInP/AlGaInP QW VCSELs: Excitation of various transverse LPij modes. Microelectronics Journal, 2008, 39, 638-640.	2.0	3
90	Structure optimisation of modern GaAs-based InGaAs/GaAs quantum-dot VCSELs for optical fibre communication. Opto-electronics Review, 2009, 17, .	2.4	3

#	Article	IF	Citations
91	Optimization of Single-Mode Photonic-Crystal Results in Limited Improvement of Emitted Power and Unexpected Broad Range of Tuning. Journal of Lightwave Technology, 2013, 31, 1360-1366.	4.6	3
92	Effect of Relief Aperture on Single-Fundamental-Mode Emission of 1.3-$mu $ m GaInNAs GaAs-Based VCSELs. IEEE Journal of Quantum Electronics, 2014, 50, 1-8.	1.9	3
93	Temperature increase within quantum-cascade lasers originating from their incomplete soldering. Photonics Letters of Poland, 2011, 3, .	0.4	3
94	Simple formulas giving temperature profiles in active layer of stripe-geometry laser diode without oxide barriers. Electronics Letters, 1983, 19, 368.	1.0	2
95	Simple formulae giving the temperature profiles in the stripe-geometry laser diodes with oxide barriers. Optical and Quantum Electronics, 1984, 16, 439-443.	3.3	2
96	The Monte-Carlo model of a light-emitting diode. Optical and Quantum Electronics, 1987, 19, 289-292.	3.3	2
97	Spreading thermal resistance of a diode-laser heat sink. Journal of Thermal Analysis, 1990, 36, 109-114.	0.6	2
98	Thermal aspects of designing CW-operated nitride VCSELs. Optical and Quantum Electronics, 1999, 31, 1179-1188.	3.3	2
99	Nitride VCSEL design for continuous-wave operation of higher-order optical modes. Applied Physics A: Materials Science and Processing, 2003, 77, 761-768.	2.3	2
100	Simulation of performance characteristics of GaInNAs vertical-cavity surface-emitting lasers. IEE Proceedings: Optoelectronics, 2003, 150, 83.	0.8	2
101	Radial optical confinement in nitride VCSELs. Journal Physics D: Applied Physics, 2003, 36, 2041-2045.	2.8	2
102	Optimisation of GaAs-based (GaIn)(NAs)//GaAs vertical-cavity surface-emitting diode lasers for high-temperature operation in 1.3-Î¼m optical-fibre communication systems. IEE Proceedings: Optoelectronics, 2004, 151, 417-420.	0.8	2
103	Cascade nitride VCSEL designs with tunnel junctions. Applied Physics A: Materials Science and Processing, 2004, 78, 315-322.	2.3	2
104	Validity of Scalar Approaches to Radiation Modes of the GaAs-Based 1.3-Î¼m Diode Lasers Designed for the Opticalâ€“Fibre Communication. Optical and Quantum Electronics, 2006, 38, 349-360.	3.3	2
105	Optimization of GaInNAs quantum-well vertical-cavity surface-emitting laser emitting at 2.33 Î¼m. Applied Physics A: Materials Science and Processing, 2014, 115, 961-969.	2.3	2
106	Designing of TJ VCSEL based on nitride materials. , 2016, , .		2
107	Basic Techniques for Fabricating Semiconductor Lasers. , 1991, , 70-106.		2
108	Thermal Properties Of Proton-implanted Top-surface Emitting Microlasers In Linear And Nonlinear Regimes. , 0, , .		1

#	ARTICLE	IF	CITATIONS
109	Thermal analysis of oxide-isolated stripe diode lasers. Journal of Thermal Analysis, 1992, 38, 1447-1462.	0.6	1
110	Available output of two-dimensional surface-emitting laser arrays. Optical and Quantum Electronics, 1997, 29, 639-649.	3.3	1
111	Thermal crosstalk in arrays of proton-implanted top-surface-emitting lasers. , 1998, 3283, 384.		1
112	Three-dimensional comprehensive self-consistent simulation of a room-temperature continuous-wave operation of GaAs-based 1.3-Î¼m quantum-dot (InGa)As/GaAs vertical-cavity surface-emitting lasers. , 0, , .		1
113	Thermal and molecular stresses in multi-layered structures of nitride devices. Semiconductor Science and Technology, 2004, 19, 667-667.	2.0	1
114	Structure Optimisation of a Possible 1.5-Î¼m GaAs-based Vertical-cavity Surface-emitting Laser Diode with the GaInNAsSb/GaNAs Quantum-well Active Region. Optical and Quantum Electronics, 2006, 38, 293-311.	3.3	1
115	Physical Analysis of a Possibility to Reach the 1.30-Î¼m Emission from the GaAs-Based VCSELs with the InGaAs/GaAs Quantum-Well Active Regions and the Intentionally Detuned Optical Cavities. Optical and Quantum Electronics, 2006, 38, 325-337.	3.3	1
116	Crucial Parameters of Photonic-Crystal Holes within Photonic-Crystal VCSEL DBR. , 2006, , .		1
117	Theoretical Analysis of Red-shift and Optical Gain in the Step-like GaInNAs/GaNAs Quantum Well. , 2006, , .		1
118	Thermal Imaging of Actively Cooled High-Power Laser Bars. , 2007, , .		1
119	Transient thermal properties of high-power diode laser bars. , 2007, , .		1
120	How exact are simplified scalar approaches to optical fields in oxide-confined stripe-geometry diode lasers?. Opto-electronics Review, 2007, 15, .	2.4	1
121	Threshold analysis of highly detuned long-wavelength GaAs-based GaInNAsSb/GaNAsQWVCSELs. Microelectronics Journal, 2008, 39, 641-643.	2.0	1
122	Performance Characteristics of GaAs-Based Oxide-Confined In(Ga)As/GaAs Quantum-Dot Vertical-Cavity Surface-Emitting Diode Lasers. , 2008, , .		1
123	Sensitivity of a VCSEL threshold performance to inaccuracies in its manufacturing. Opto-electronics Review, 2010, 18, .	2.4	1
124	Electrically Pumped Vertical-External-Cavity Surface-Emitting Lasers With Patterned Tunnel Junction for Single Transversal-Mode Emission. IEEE Journal of Selected Topics in Quantum Electronics, 2015, 21, 485-492.	2.9	1
125	Transverse-mode selectivity in antimonide-based vertical-cavity surface-emitting lasers. , 2015, , .		1
126	Impact of thermal crosstalk between emitters on power roll-over in nitride-based blue-violet laser bars. Semiconductor Science and Technology, 2017, 32, 025008.	2.0	1

#	ARTICLE	IF	CITATIONS
127	Quantum-Cascade Vertical-Cavity Surface-Emitting Laser (QC-VCSEL). , 2018, , .		1
128	Improved thermal properties of etched-well surface-emitting lasers with highly-doped P-cladding. , 1992, , .		1
129	Quantum-cascade vertical-cavity surface-emitting laser integrated with monolithic high-contrast grating. , 2018, , .		1
130	Simulation of photonic crystal diode lasers with plane-wave admittance method. , 0, , .		0
131	The self-consistent method for determination of a band structure in photonic crystals with frequency-dependent dielectric constants. , 0, , .		0
132	Threshold current of oxide-insulated stripe laser diodes. Soviet Journal of Quantum Electronics, 1982, 12, 348-350.	0.1	0
133	Thermal Model Of The Homojunction Burrus-Type Light-Emitting Diode. , 1986, , .		0
134	Reply: Thermal model of laser diode arrays. Electronics Letters, 1987, 23, 458.	1.0	0
135	Comment on â€œThe dynamic temperature distributions in stripe geometry lasersâ€• Journal of Luminescence, 1990, 46, 419-420.	3.1	0
136	Thermal optimization of a construction of a double-heterostructure GaAs/(AlGa)As diode laser. Journal of Thermal Analysis, 1990, 36, 1039-1047.	0.6	0
137	Note to reply of R.F. Ormondroyd. Journal of Luminescence, 1990, 46, 423.	3.1	0
138	Is The Thermal Time "Constant" Of A Diode Laser Really Constant?. , 1990, , .		0
139	Spreading thermal resistance of a diode-laser heat sink. Optical and Quantum Electronics, 1991, 23, 427-432.	3.3	0
140	Thermal Effects In Monolithically Integrated Two-dimensional Arrays Of Etched-well Surface-emitting Diode Lasers. , 0, , .		0
141	Optimal Design Of Etched-well GaAs/AlGaAs Surface-emitting Diode Lasers. , 0, , .		0
142	Thermal crosstalk in two-dimensional arrays of vertical-cavity surface-emitting diode lasers. , 0, , .		0
143	High-order transverse modes in vertical-cavity surface-emitting lasers. , 1998, , .		0
144	Optimal configurations of active regions in nitride VCSELs. , 0, , .		0

#	Article	IF	Citations
145	(InGa)As/GaAs quantum-dot diode lasers for 1.3-Î¼m optical fibre communication. , 0, , .		0
146	Structure optimisation of 1.3â€…Î¼m (GaIn)(NAs)â^•GaAs in-plane lasers. IEE Proceedings: Optoelectronics, 2003, 150, 56.	0.8	0
147	Higher-Order Transverse Modes in Possible Nitride VCSELs. Physica Status Solidi C: Current Topics in Solid State Physics, 2003, 0, 48-51.	0.8	0
148	Methods to enhance mode selectivity of higher-output vertical-cavity surface-emitting diode lasers. , 2005, , .		0
149	Mode selectivity in oxide-confined vertical-cavity surface-emitting lasers. , 0, , .		0
150	Comparative Analysis of Various Designs of Oxide-Confined Vertical-Cavity Surface-Emitting Diode Lasers. , 2006, , .		0
151	<title>Physics of an operation of vertical cavity surface emitting lasers with oxide apertures</title>. , 2006, , .		0
152	Optical Design of Vertical-Cavity Lasers. , 0, , 447-466.		0
153	Investigation of operational characteristics and possibility of obtaining highly detuned GaInNAsSb VCSEL. Physica Status Solidi C: Current Topics in Solid State Physics, 2008, 5, 445-448.	0.8	0
154	Comparative Analysis of Thermal Properties of Various Quantum-Cascade Lasers. , 2008, , .		0
155	Comparison of the room-temperature threshold operation of index- and gain-guided oxide-confined VCSELs. , 2008, , .		0
156	Unusual transverse-mode selectivity in some detuned VCSELs. , 2008, , .		0
157	Comparative analysis of various methods to reach the 1.3-µm emission in GaInNAs/GaAs QW VCSELs. , 2009, , .		0
158	Continues-wave single-mode operation of quantum-dot photonic-crystal 1300 nm VCSEL. , 2009, , .		0
159	Analysis of excitation of higher-order transverse modes in large-size oxide-confined VCSELs. , 2009, , .		0
160	Pulse-regime single-mode operation of antiwaveguide photonic-crystal 1300-nm VCSEL. , 2010, , .		0
161	Methods to improve performance of the 1.3-μm oxide-confined GaInNAs/GaAs QW VCSELs. , 2010, , .		0
162	Elimination of an impact of mechanical stresses on an operation of nitride light-emitting diodes. , 2011, , .		0

#	Article	IF	Citations
163	Current spreading modification to enhance single-fundamental-mode VCSEL operation at higher temperatures. Opto-electronics Review, 2011, 19, .	2.4	0
164	Structure modifications of oxide-confined GaInNAs VCSELs for the second-generation optical-fibre communication. Physica Status Solidi C: Current Topics in Solid State Physics, 2011, 8, 1601-1604.	0.8	0
165	A new structure of nitride light-emitting diodes without polarization effects. Physica B: Condensed Matter, 2012, 407, 3960-3964.	2.7	0
166	A method used to enhance mode selectivity of VCSELs with large oxide apertures. , 2013, , .		0
167	Why phtonic-crystal VCSELs do not provide high power emission in the single-mode regime?. , 2013, , .		0
168	Thermal resistance of GaAs/AlAs superlattices used in modern light-emitting diodes. Opto-electronics Review, 2014, 22, .	2.4	0
169	Numerical simulation of 1.3-μm vertical-external-cavity surface-emitting lasers. , 2014, , .		0
170	Impact of structure mounting of nitride laser bars on the emitted optical power. , 2016, , .		0
171	Performance characteristics of GaSb-based TJ-VCSELs with emission wavelength above 2.6 Âµm. , 2016, , .		0
172	Monolithic reflector for infrared radiation. Proceedings of SPIE, 2017, , .	0.8	0
173	Modes Distribution in Quantum-Cascade Vertical-Cavity Surface-Emitting Laser (VCSEL). , 2018, , .		0
174	Photonic crystal used to increase extraction efficiencyof ZnO light-emitting diodes. Photonics Letters of Poland, 2010, 2, .	0.4	0
175	Inverted-relief cavity used in VCSELs to suppress higher-order transverse modes. Photonics Letters of Poland, 2014, 6, .	0.4	0
176	The Monte-Carlo Simulation Of The Surface Light Emitting Diode (LED) Operation.. Proceedings of SPIE, 1990, , .	0.8	0
177	Reliability of LEDs and Junction Lasers. , 1991, , 436-462.		0
178	<title>Self-consistent analytical models of semiconductor vertical-cavity surface-emitting lasers</title>. , 1997, , .		0
179	Lasery pÃ³Å,przewodnikowe. Przeglad Elektrotechniczny, 2015, 1, 149-151.	0.2	0
180	Lasery pÃ³Å,przewodnikowe pompowane promieniowaniem sÅ,onecznym. Przeglad Elektrotechniczny, 2016, 1, 143-146.	0.2	0

#	Article	IF	Citations
181	PoczÄ…tek i rozwÃ³j pÃ³Å‚przewodnikowych laserÃ³w VCSEL. Przeglad Elektrotechniczny, 2017, 1, 3-10.	0.2	0
182	New structure of semiconductor lasers: quantum-cascade vertical-cavity surface-emitting laser (QC) Tj ETQq0 0 0 rgBT /Overlock 10 Tf 5		0